

**WHAT IS CLAIMED:**

- 1 1. A method of controlling the focus errors of a photolithographic exposure tool  
2 comprising the steps of:  
3  
4 a) making measurements of three dimensional feature changes in a photosensitive  
5 resist;  
6  
7 b) generating a function which defines a relationship between said feature  
8 measurements and said focus of said photolithographic exposure tool;  
9  
10 c) computing from said function a best profile focus value wherein said best profile  
11 focus value is used for controlling the focus errors of said photolithographic exposure  
12 tool.
- 1 2. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 1 wherein said step a) comprises:  
3  
4 exposing a focus expose matrix wafer by varying exposure levels and focus conditions  
5 wherein said feature measurements include a plurality of edge width versus focus data  
6 points for any given one of said exposure levels.
- 1 3. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 1, wherein said measurements of said step a) are stored.
- 1 4. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 2, wherein said plurality of edge width versus focus data points are  
3 plotted for each of said exposure levels.

1 5. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 2 wherein said plurality of edge width vs. focus data points are  
3 retained for a default exposure level.

1 6. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 5, wherein step b) comprises computing a derived an equation which  
3 characterizes said plurality of edge width vs. focus data points to define said function.

1 7. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 6, wherein a second derivative of said derived equation is solved to  
3 obtain said best profile focus value for said feature where said second derivative is  
4 equal to zero.

1 8. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 7, wherein measurements of a specific three dimensional feature type  
3 are made across an exposure field on a production wafer.

1 9. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 8, wherein said three dimensional measurements comprise edge width  
3 measurements

1 10. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 9, wherein an average of said edge width measurements is calculated.

1 11. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 10, wherein said average edge width is input to said function to derive  
3 a measured focus of said feature type on said production wafer.

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12. The method of controlling the focus errors of a photolithographic exposure tool as claimed in Claim 11, wherein a difference between said measured focus and said best profile focus value is fed back to said tool thereby controlling focus errors of said tool.

1 13. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 11, wherein a difference between said measured focus and an optimal  
3 product focus offset is fed back to said tool thereby controlling focus errors of said tool.

1 14. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 6, wherein said equation defining said function is a cubic of the form:

$$3 \qquad y = Ax^3 - Bx^2 + Cx + D,$$

4 where **y** is the edge width, **x** is the focus, **A**, **B**, **C** and **D** are empirically derived  
5 coefficients.

1 15. The method of controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 7, wherein said second derivative solving step results in an equation:

$$3 \qquad 6A_x + 2B = 0,$$

4 wherein the solution  $x$  representing said best profile focus value is governed by the  
5 equation:

6  $x = -1/3*(B/A).$

1 16. A method of controlling tilt errors of a photolithographic exposure tool  
2 comprising:

3 a) making measurements of three dimensional feature changes in a  
4 photosensitive resist;

6    b) generating a function which defines a relationship between said feature  
7    measurements and a focus of said photolithographic exposure tool;

9 c) computing from said function x/y tilt values wherein said x/y tilt values are used to  
10 control said tilt errors of said photolithographic exposure tool thereby achieving an  
11 optimum x/y tilt offset.

1 17. The method of controlling tilt errors of a photolithographic exposure tool as  
2 claimed in Claim 16, wherein step a) comprises:  
3  
4 exposing a focus expose matrix wafer by varying exposure levels and focus conditions  
5 wherein said feature measurements include a plurality of edge width vs. focus data  
6 points for any one of said exposure levels.  
7

1 18. The method of controlling tilt errors of a photolithographic exposure tool as  
2 claimed in Claim 16 wherein step b) comprises computing a derived equation which  
3 characterizes said plurality of edge width vs. focus data points at a default exposure  
4 level to define said function.

1 19. The method of controlling the tilt of a photolithographic exposure tool as claimed  
2 in Claim 16, wherein step c) comprises:  
3

4 a) using said function to obtain said x/y tilt values including a y tilt value,  $\theta_y$ ,  
5 corresponding to a trigonometric relationship that relates a distance,  $D_y$  between  
6 measurement sites on a production wafer, an edge width derived focus,  $F1_y$  taken from  
7 an extreme lower position of an exposure field, and an edge width derived focus,  $F2_y$ ,  
8 taken from an extreme upper position of the exposure field;  
9  
10 b) using said function to obtain said adjustments including an x tilt value,  $\theta_x$ ,  
11 corresponding to a trigonometric relationship that relates a distance  $D_x$  between  
12 measurement sites on the wafer, and edge width derived focus  $F1_x$  taken from the

13 extreme left position of said exposure field, and an edge width derived focus,  $F2_x$  taken  
14 from the extreme right position of said exposure field;

15

16 c) feeding back said x tilt value,  $\theta_x$  to said photolithographic exposure tool; and

17

18 d) feeding back said y tilt value,  $\theta_y$  to said photolithographic exposure tool.

1 20. The method of controlling the tilt of a photolithographic exposure tool as claimed  
2 in Claim 19, wherein said y tilt value,  $\theta_y$ , is governed by the equation,

3 
$$\theta_y = \arctan((F2_y - F1_y)/D_y); \text{ and,}$$

4 said x tilt value,  $\theta_x$  is governed by the equation,

5 
$$\theta_x = \arctan((F2_x - F1_x)/D_x).$$

6

1 21. The method of controlling the tilt of a photolithographic exposure tool as claimed  
2 in Claim 20, wherein said y tilt value in microradians being governed by the equation,

3 
$$\theta_y = \arctan((F2_y - F1_y)/D_y) * (\pi/180) * 1E6; \text{ and,}$$

4 said x tilt value in microradians is governed by the equation,

5 
$$\theta_x = \arctan((F2_x - F1_x)/D_x) * (\pi/180) * 1E6.$$

6

1 22. A system for controlling the focus errors of a photolithographic exposure tool  
2 comprising:

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4 a) means for measuring three dimensional feature changes in a photosensitive resist;

5

6 b) function generation means for defining a relationship between said feature  
7 measurements and said focus of said photolithographic exposure tool;

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1 28. The system for controlling the focus errors of a photolithographic exposure tool as  
2 claimed in Claim 26 further comprising:

3  
4 a) means for obtaining x/y tilt values including a y tilt value,  $\theta_y$ , corresponding to a  
5 trigonometric relationship that relates a distance,  $D_y$  between measurement sites on said  
6 production wafer, an edge width derived focus,  $F1_y$  taken from the extreme lower  
7 position of an exposure field, and an edge width derived focus,  $F2_y$ , taken from an  
8 extreme upper position of the exposure field;

9  
10 b) means for obtaining said x/y tilt values including an x tilt value,  $\theta_x$ , corresponding  
11 to a trigonometric relationship relating a distance  $D_x$  between measurement sites on the  
12 wafer, and edge width derived focus  $F1_x$  taken from the extreme bottom position of said  
13 exposure field, and an edge width derived focus,  $F2_x$  taken from the extreme top  
14 position of said exposure field;

15  
16 c) means for correcting said photolithographic exposure tool with said tilt values,  $\theta_x$   
17 ,  $\theta_y$ .

1 29. A computer program product comprising:

2  
3 a computer usable medium having computer readable program code embodied therein  
4 for implementing focus error control of a photolithographic exposure tool, the computer  
5 readable program code in said computer program product comprising:

6  
7 a) first computer readable program code for causing a computer to measure three  
8 dimensional profile changes of a feature in a photosensitive resist;

9  
10 b) second computer readable program code for causing the computer to store said  
11 measurements;

12

13 c) third computer readable program code for causing the computer to generate a  
14 function which defines a relationship between said feature measurements and said focus  
15 of said photolithographic exposure tool;

16

17 d) fourth computer readable program code for causing the computer to calculate from  
18 said function a best profile focus value wherein said best profile focus value is used to  
19 control the focus errors of said photolithographic exposure tool.

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1 30. The computer program product as claimed in Claim 29 comprising fifth computer  
2 program code for inputting to said function an average of measurements made on a  
3 specific three dimensional feature type across an exposure field on a production wafer  
4 to derive a measured focus of said specific three dimensional feature type on said  
5 production wafer.

1 31. The computer program product as claimed in Claim 30 comprising sixth computer  
2 program code for computing a difference between said measured focus and said best  
3 profile focus value, then feeding back said difference to said photolithographic exposure  
4 tool wherein said focus errors of said photolithographic exposure tool are controlled.

1 32. The computer program product as claimed in Claim 30 comprising:  
2 seventh computer readable program code for causing the computer to calculate x/y tilt  
3 values from said measured focus, wherein said x/y tilt values are used to control tilt  
4 errors of said photolithographic exposure tool whereby an optimum x/y tilt offset is  
5 achieved.

1 33. A method of checking the focus of a photolithographic exposure tool comprising:

2



- 3 a) making a data collection of EW data associated with said exposure tool versus  
4 barometric pressure data over a predetermined time period;  
5  
6 b) storing said data collection;  
7  
8 c) making a comparison between a current focus setting of said exposure tool exposed  
9 to a current barometric pressure and said stored data collection;  
10  
11 d) notifying a user that a tool problem exists based on said comparison.

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